

# SMD Schottky Barrier Diodes

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## CDBW0520 - CDBW0540

**Voltage: 20- 40 Volts**

**Current: 0.5 Amp**



### Feature

Low turn-on voltage

Fast switching

PN junction guard ring for transient and ESD protection

### Mechanical data

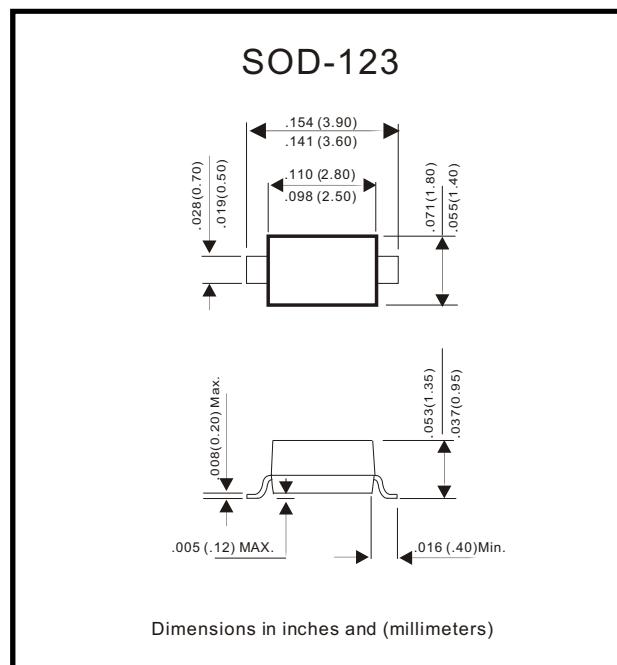
Case: SOD-123, molded plastic

Terminals: solderable per MIL-STD-750, method 2026

Polarity: Indicated by cathode band

Mounting position: Any

Weight: 0.008 grams



### Maximum Ratings and Electrical Characteristics

Parameter	Symbol	CDBW0520	CDBW0530	CDBW0540	Unit
Max.RepetitivePeak Reverse Voltage	V <sub>RRM</sub>	20	30	40	V
Max. DC Blocking Voltage	V <sub>DC</sub>	14	21	28	V
Max. RMS Voltage	V <sub>RMS</sub>	20	30	40	V
Peak Surge Forward Current 8.3ms single halfsine-wave Sine-wave superimposed on Rate load (JEDEC )	I <sub>FSM</sub>		5.5		A
Max. AverageForward Current	I <sub>o</sub>		0.5		A
Max. Forward Current at 0.1 A 0.5 A	V <sub>F</sub>	0.3 0.385	0.375 0.430	0.51	V
Max. Reverse Current	I <sub>R</sub>	0.075 @ V <sub>R</sub> =10V 0.25 @ V <sub>R</sub> =20V	0.02 @ V <sub>R</sub> =15V 0.13 @ V <sub>R</sub> =30V	0.01 @ V <sub>R</sub> =20V 0.02 @ V <sub>R</sub> =40V	mA
Max. Thermal Resistance	R <sub>θ JA</sub> R <sub>θ JL</sub>		206 150		°C/W
Operating junction temperature	T <sub>j</sub>		-55 to +125		°C
Storage temperature	T <sub>STG</sub>		-55 to +125		°C

Note 1: Thermal resistance from junction to ambient and junction to to lead P.C.B. Mounted on 0.2 x 0.2 copper pad areas

## RATING AND CHARACTERISTIC CURVES (CDBW0520-0540)

Fig. 1 - Reverse Characteristics

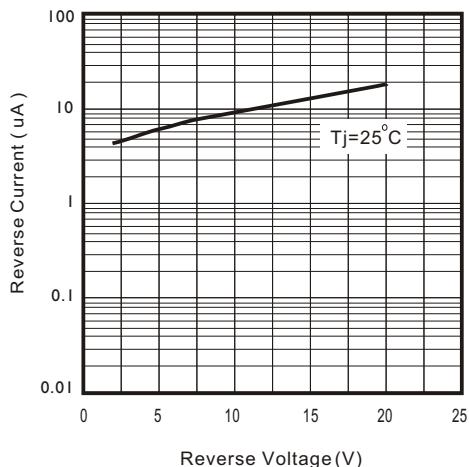


Fig. 2 - Reverse Characteristics

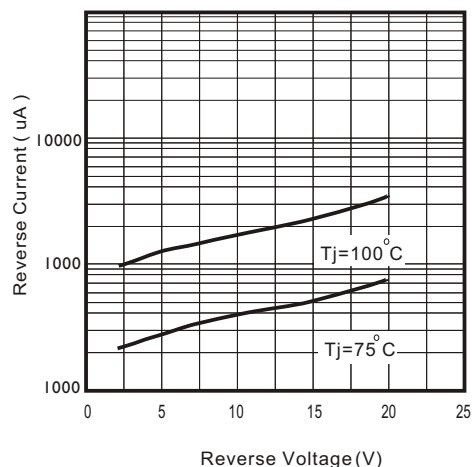


Fig. 3 - Forward Characteristics

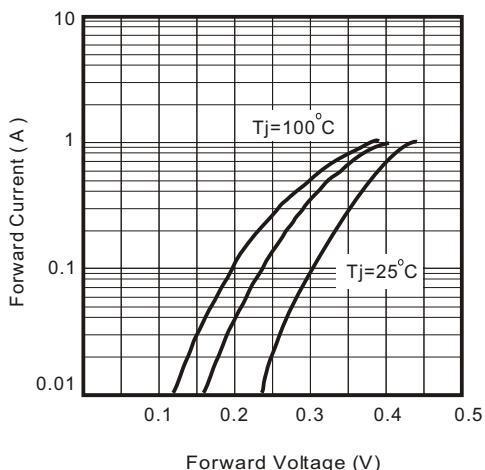


Fig. 4 - Current Derating Curve

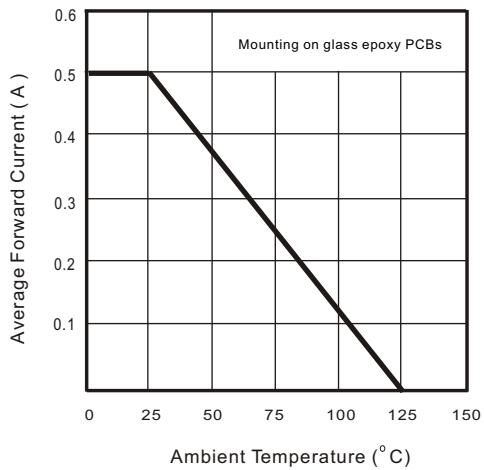


Fig. 3 - Capacitance Between Terminals characteristics

